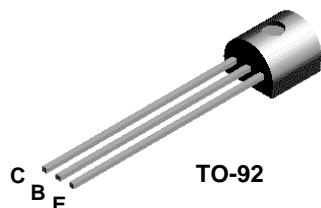
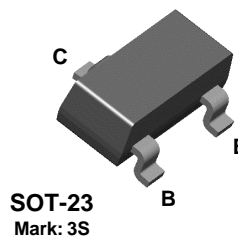


2N5551



MMBT5551



NPN General Purpose Amplifier

This device is designed for general purpose high voltage amplifiers and gas discharge display drivers.

Absolute Maximum Ratings*

TA = 25°C unless otherwise noted

| Symbol | Parameter | Value | Units |
|-----------------------------------|--|-------------|-------|
| V _{CEO} | Collector-Emitter Voltage | 160 | V |
| V _{CBO} | Collector-Base Voltage | 180 | V |
| V _{EBO} | Emitter-Base Voltage | 6.0 | V |
| I _C | Collector Current - Continuous | 600 | mA |
| T _J , T _{stg} | Operating and Storage Junction Temperature Range | -55 to +150 | °C |

*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:

- 1) These ratings are based on a maximum junction temperature of 150 degrees C.
- 2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Thermal Characteristics

TA = 25°C unless otherwise noted

| Symbol | Characteristic | Max | | Units |
|------------------|---|--------|-----------|-------|
| | | 2N5551 | *MMBT5551 | |
| P _D | Total Device Dissipation Derate above 25°C | 625 | 350 | mW |
| | | 5.0 | 2.8 | mW/°C |
| R _{θJC} | Thermal Resistance, Junction to Case | 83.3 | | °C/W |
| R _{θJA} | Thermal Resistance, Junction to Ambient | 200 | 357 | °C/W |

* Device mounted on FR-4 PCB 1.6" X 1.6" X 0.06."

NPN General Purpose Amplifier

(continued)

2N5551 / MMBT5551

Electrical Characteristics

TA = 25°C unless otherwise noted

| Symbol | Parameter | Test Conditions | Min | Max | Units |
|--------|-----------|-----------------|-----|-----|-------|
|--------|-----------|-----------------|-----|-----|-------|

OFF CHARACTERISTICS

| | | | | | |
|---------------|---------------------------------------|--|-----|----------|---------------------|
| $V_{(BR)CEO}$ | Collector-Emitter Sustaining Voltage* | $I_C = 1.0 \text{ mA}, I_B = 0$ | 160 | | V |
| $V_{(BR)CBO}$ | Collector-Base Breakdown Voltage | $I_C = 100 \mu\text{A}, I_E = 0$ | 180 | | V |
| $V_{(BR)EBO}$ | Emitter-Base Breakdown Voltage | $I_E = 10 \mu\text{A}, I_C = 0$ | 6.0 | | V |
| I_{CBO} | Collector Cutoff Current | $V_{CB} = 120 \text{ V}, I_E = 0,$ $V_{CB} = 120 \text{ V}, I_E = 0, T_A = 100^\circ\text{C}$ | | 50 50 | nA μA |
| I_{EBO} | Emitter Cutoff Current | $V_{EB} = 4.0 \text{ V}, I_C = 0$ | | 50 | nA |

ON CHARACTERISTICS

| | | | | | |
|---------------|--------------------------------------|--|----------------|--------------|--------|
| h_{FE} | DC Current Gain | $I_C = 1.0 \text{ mA}, V_{CE} = 5.0 \text{ V}$ $I_C = 10 \text{ mA}, V_{CE} = 5.0 \text{ V}$ $I_C = 50 \text{ mA}, V_{CE} = 5.0 \text{ V}$ | 80 80 30 | 250 | |
| $V_{CE(sat)}$ | Collector-Emitter Saturation Voltage | $I_C = 10 \text{ mA}, I_B = 1.0 \text{ mA}$ $I_C = 50 \text{ mA}, I_B = 5.0 \text{ mA}$ | | 0.15 0.20 | V V |
| $V_{BE(sat)}$ | Base-Emitter Saturation Voltage | $I_C = 10 \text{ mA}, I_B = 1.0 \text{ mA}$ $I_C = 50 \text{ mA}, I_B = 5.0 \text{ mA}$ | | 1.0 1.0 | V V |

SMALL SIGNAL CHARACTERISTICS

| | | | | | |
|-----------|----------------------------------|---|-----|-----|-----|
| f_T | Current Gain - Bandwidth Product | $I_C = 10 \text{ mA}, V_{CE} = 10 \text{ V},$ $f = 100 \text{ MHz}$ | 100 | 300 | MHz |
| C_{obo} | Output Capacitance | $V_{CB} = 10 \text{ V}, I_E = 0,$ $f = 1.0 \text{ MHz}$ | | 6.0 | pF |
| C_{ibo} | Input Capacitance | $V_{BE} = 0.5 \text{ V}, I_C = 0,$ $f = 1.0 \text{ MHz}$ | | 20 | pF |
| h_{fe} | Small-Signal Current Gain | $I_C = 1.0 \text{ mA}, V_{CE} = 10 \text{ V},$ $f = 1.0 \text{ kHz}$ | 50 | 250 | |
| NF | Noise Figure | $I_C = 250 \mu\text{A}, V_{CE} = 5.0 \text{ V},$ $R_S = 1.0 \text{ k}\Omega, f = 10 \text{ Hz to } 15.7 \text{ kHz}$ | | 8.0 | dB |

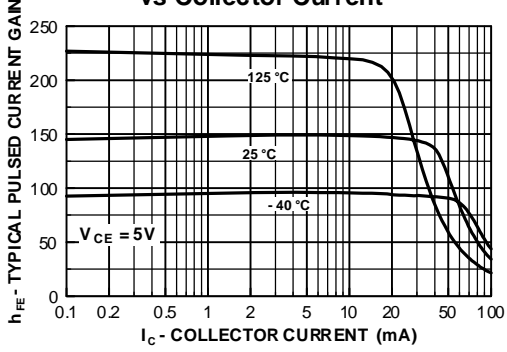
*Pulse Test: Pulse Width $\leq 300 \mu\text{s}$, Duty Cycle $\leq 2.0\%$

Spice Model

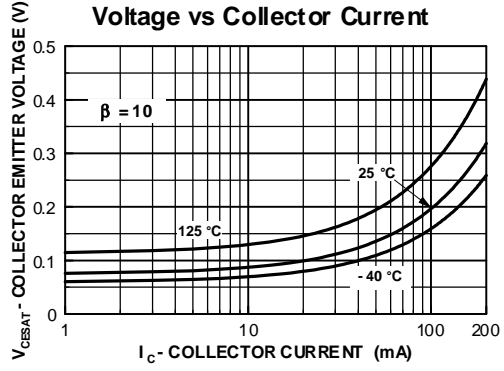
NPN (Is=2.511f Xti=3 Eg=1.11 Vaf=100 Bf=242.6 Ne=1.249 Ise=2.511f Ikf=.3458 Xtb=1.5 Br=3.197 Nc=2 Isc=0 Ikr=0 RC=1 Cjc=4.883p Mjc=.3047 Vjc=.75 Fc=.5 Cje=18.79p Mje=.3416 Vje=.75 Tr=1.202n Tf=560p Itf=50m Vtf=5 Xtf=8 Rb=10)

Typical Characteristics

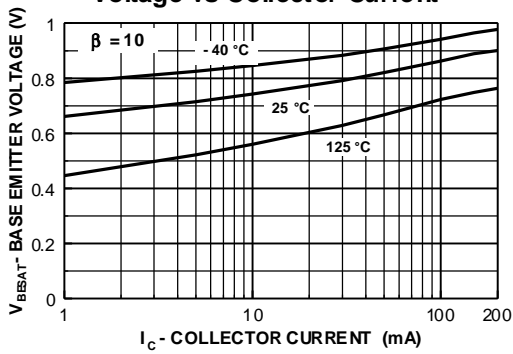
Typical Pulsed Current Gain vs Collector Current



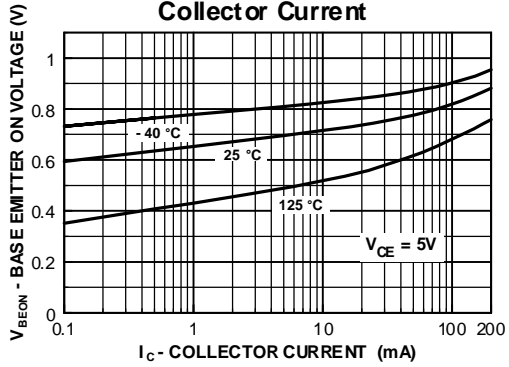
Collector-Emitter Saturation Voltage vs Collector Current



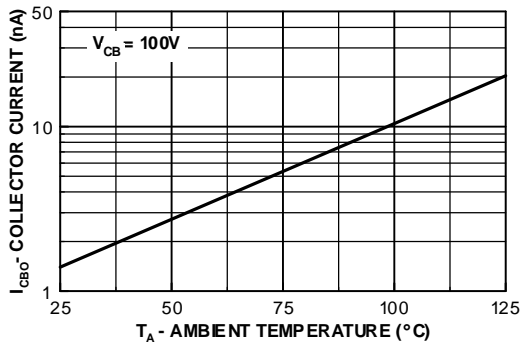
Base-Emitter Saturation Voltage vs Collector Current



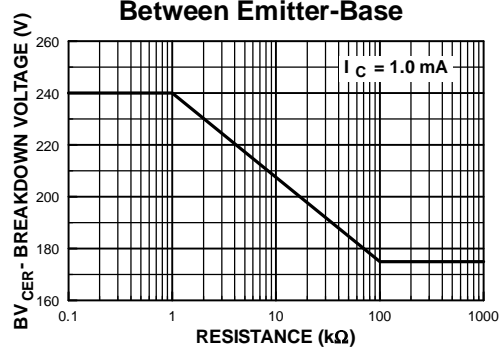
Base Emitter ON Voltage vs Collector Current



Collector-Cutoff Current vs. Ambient Temperature



Collector-Emitter Breakdown Voltage with Resistance Between Emitter-Base



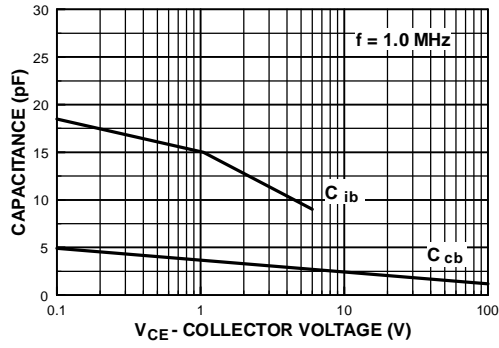
NPN General Purpose Amplifier

(continued)

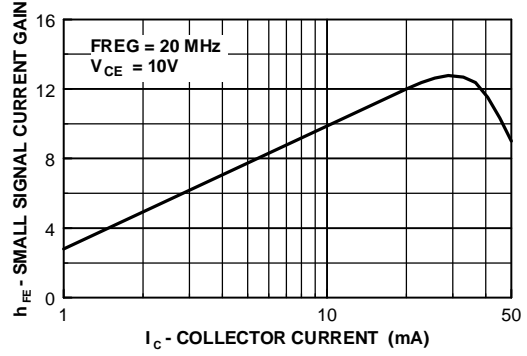
2N5551 / MMBT5551

Typical Characteristics (continued)

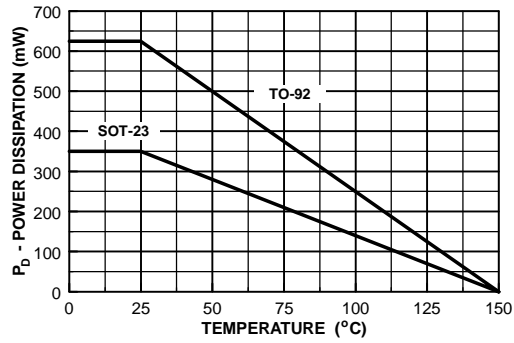
Input and Output Capacitance vs Reverse Voltage



Small Signal Current Gain vs Collector Current



Power Dissipation vs Ambient Temperature



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